LM803ESDCP18-0.22x0.36

Features

- 1-Channel Bi-directional ESD diode
- Low Operating Voltage: 2.8-3.3V
- Ultra Low Leakage: nA Level
- Low Clamping Voltage
- Response time is typically < 1 ns
- RoHS compliant
- Ultra Small Die Size, suitable for DFN1006 or DFN0603 package
- Complies with IEC 61000-4-2 standards:

  Air discharge: ±30kV

  Contact discharge: ±30kV

Die Top-View

Circuit Diagram

Wafer Information

Item	Description
Wafer size	8 inch
Wafer thickness	750±20μm
Die Size (Include scribe lane)	220μm x 360μm
Bond Pad Opening	150μm x 290μm
Scribe lane width	50μm
Gross die per wafer	370, 000 dies
Top metal for wire bond	4μm AlSiCu
Back side metal	NONE

Absolute Maximum Ratings (TA=25℃ unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20μs)	P_{pk}	240	W
ESD per IEC61000-4-2 (Air) ESD per IEC61000-4-2 (Contact)	V_{ESD}	±30 ±30	kV
Operating Temperature Range	T_J	-55 to +150	℃
Storage Temperature Range	T_{stg}	-55 to +150	℃

Electrical Characteristics (TA=25℃ unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V_{RWM}			3.3	V	
Breakdown Voltage	V_{BR}	3.8	4.3	5.0	V	I_T=1mA
Leakage Current	I_{Leak}	1		200	nA	V_{RWM}=3.3V
Clamping Voltage	V_C			6.5	V	I_{PP}=1A,Tp=8/20μs
Clamping Voltage	V_C			12	V	I_{PP}=18A,Tp=8/20μs
Junction Capacitance	C_J		30	50	pF	V_R=0V, f=1MHz

Note: Electrical parameters are only for die, performance may alter after assembly.

NOTICE

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Shanghai Leiditech Electronic Technology Co., Ltd.
Email: sale1@leiditech.com
Tel : +86- 021 50828806
Fax : +86- 021 50477059